



No.3712

2SC4547

NPN Planar Silicon Darlington Transistor

Driver Applications

Applications

- Suitable for use in switching of L load (motor drivers, printer hammer drivers, relay drivers).

Features

- High DC current gain.
 - Large current capacity and wide ASO.
 - Contains zener diode of 95 ± 10 V between collector and base.
 - Uniformity in collector-to-base breakdown voltage due to adoption of accurate impurity-diffusion process.
 - High inductive load handling capability.

Absolute Maximum Ratings at Ta = 25°C

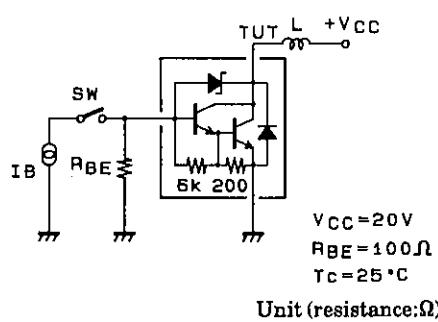
Absolute Maximum Ratings at $T_A = 25^\circ C$		unit
Collector-to-Base Voltage	V_{CBO}	※ 85 V
Collector-to-Emitter Voltage	V_{CEO}	※ 85 V
Emitter-to-Base Voltage	V_{EBO}	6 V
Collector Current	I_C	3 A
Peak Collector Current	i_{cp}	5 A
Base Current	I_B	0.5 A
Collector Dissipation	P_C	1.75 W
$T_c = 25^\circ C$		
Junction Temperature	T_j	30 W
Storage Temperature	T_{stg}	150 °C
		-55 to +150 °C

※ : With Zener diode (95 ± 10 V).

Electrical Characteristics at $T_a \equiv 25^\circ\text{C}$

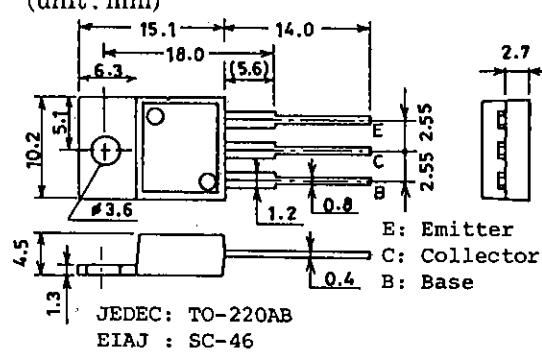
Electrical Characteristics at $T_A = 25^\circ C$			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 70V, I_E = 0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			3	mA
DC Current Gain	h_{FE}	$V_{CE} = 3V, I_C = 1.5A$	2000	6000		
Gain-Bandwidth Product	f_T	$V_{CE} = 5V, I_C = 1.5A$		50		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 1.5A, I_B = 3mA$		0.9	1.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 1.5A, I_B = 3mA$			2.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 0.1mA, I_E = 0$	85	95	105	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	85	95	105	V
Inductive Load Voltage	$E_{s/b}$	$L = 100mH, R_{BE} = 100\Omega$	15			mJ

Es/b Test Circuit

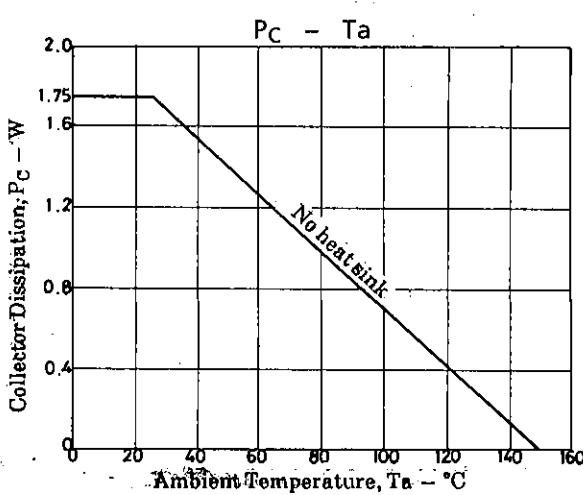
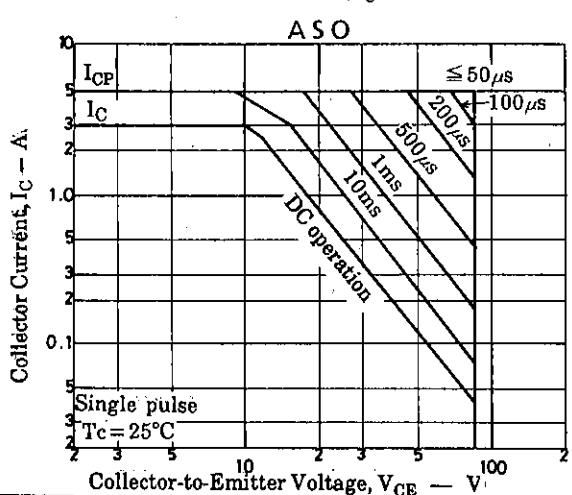
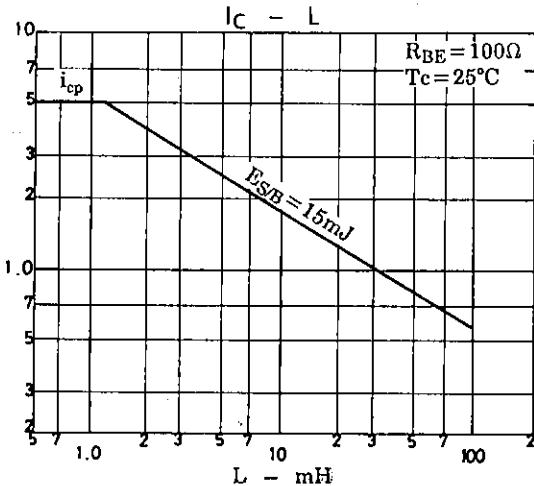
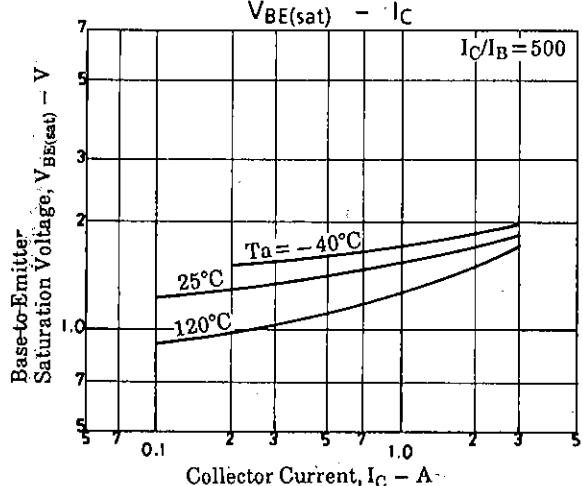
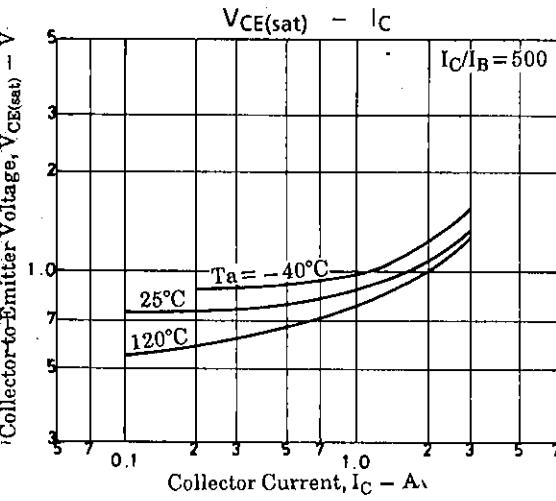
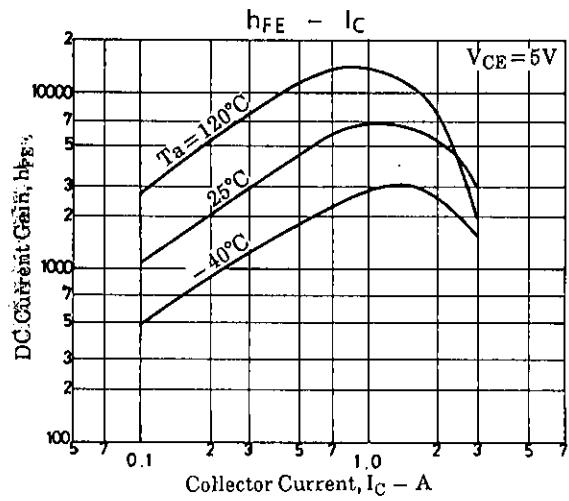
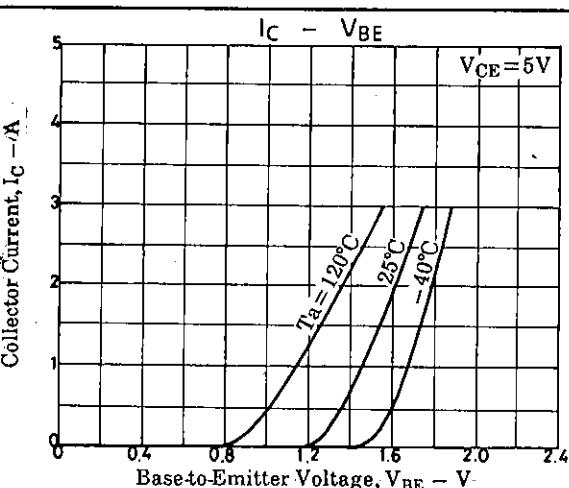
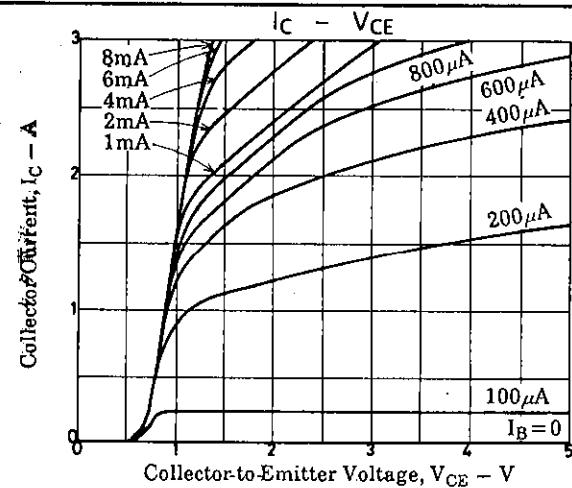


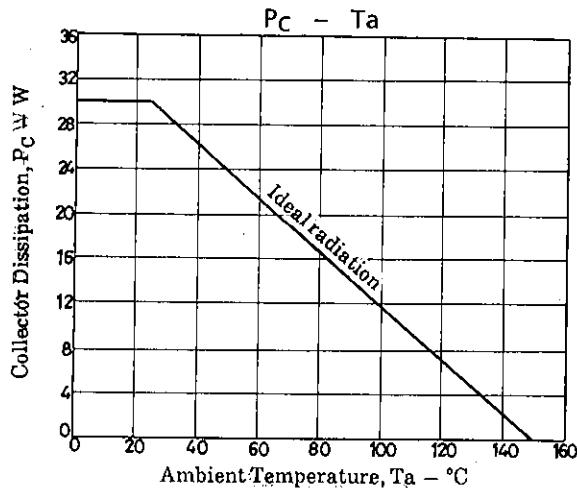
Package Dimensions 2010B

(unit : mm)



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